

Dual P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 12	0.018 at $V_{GS} = - 4.5$ V	- 8.9
	0.022 at $V_{GS} = - 2.5$ V	- 8.1
	0.028 at $V_{GS} = - 1.8$ V	- 3.6

FEATURES

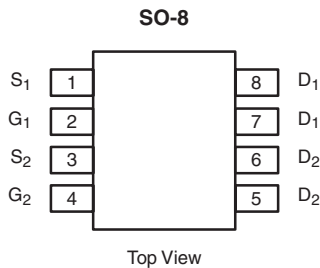
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Advanced High Cell Density Process
- Compliant to RoHS Directive 2002/95/EC



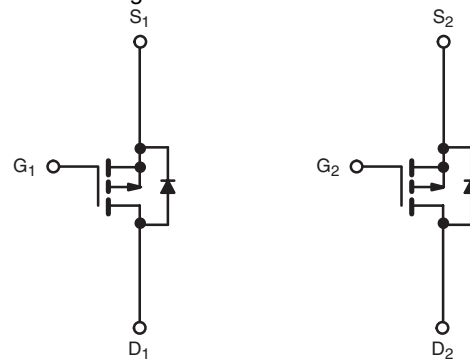
RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Load Switching



Ordering Information: Si4931DY-T1-E3 (Lead (Pb)-free)
Si4931DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

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ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage	V_{DS}	- 12		V
Gate-Source Voltage	V_{GS}	± 8		
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	- 8.9	- 6.7
		$T_A = 70$ °C	- 7.1	- 5.4
Pulsed Drain Current	I_{DM}	- 30		A
Continuous Source Current (Diode Conduction) ^a	I_S	- 1.7	- 0.9	
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	2.0	1.1
		$T_A = 70$ °C	1.3	0.7
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ s	46	62.5	°C/W
		Steady State	80	110	
Maximum Junction-to-Foot (Drain)	R_{thJF}	24	32		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.



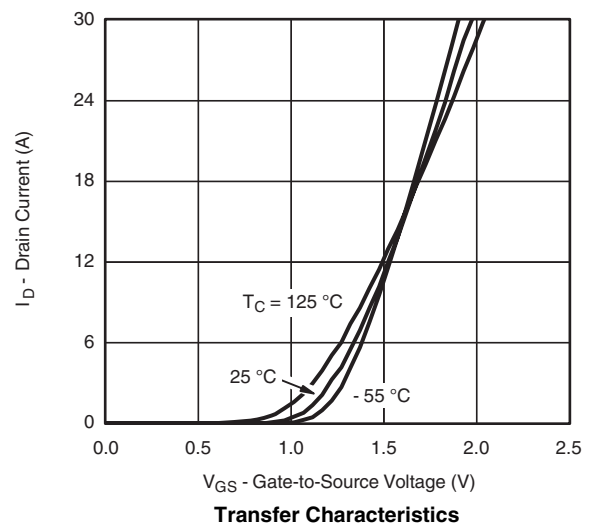
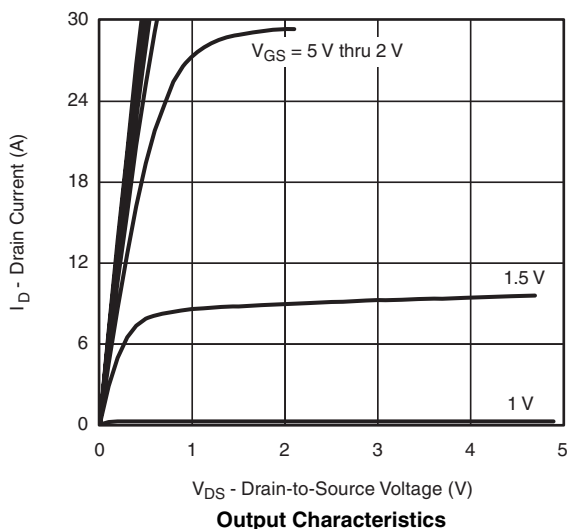
SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -350\ \mu\text{A}$	-0.4		-1.0	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 8\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -12\ \text{V}, V_{GS} = 0\ \text{V}$			-1	μA
		$V_{DS} = -12\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 55^\circ\text{C}$			-5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\ \text{V}, V_{GS} = -4.5\ \text{V}$	-30			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\ \text{V}, I_D = -8.9\ \text{A}$		0.0145	0.018	Ω
		$V_{GS} = -2.5\ \text{V}, I_D = -8.1\ \text{A}$		0.018	0.022	
		$V_{GS} = -1.8\ \text{V}, I_D = -3.6\ \text{A}$		0.023	0.028	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -6\ \text{V}, I_D = -8.9\ \text{A}$		26		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.7\ \text{A}, V_{GS} = 0\ \text{V}$		-0.7	-1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -6\ \text{V}, V_{GS} = -4.5\ \text{V}, I_D = -8.9\ \text{A}$		34.5	52	nC
Gate-Source Charge	Q_{gs}		5.1			
Gate-Drain Charge	Q_{gd}		9.6			
Gate Resistance	R_g			9		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -6\ \text{V}, R_L = 6\ \Omega$ $I_D \cong -1\ \text{A}, V_{GEN} = -4.5\ \text{V}, R_g = 6\ \Omega$		25	40	ns
Rise Time	t_r		46	70		
Turn-Off Delay Time	$t_{d(off)}$		230	345		
Fall Time	t_f		155	235		
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -1.7\ \text{A}, dI/dt = 100\ \text{A}/\mu\text{s}$		128	200	

Notes:

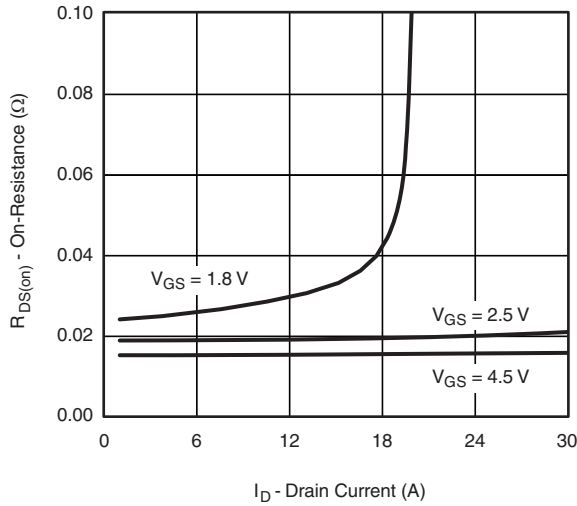
- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

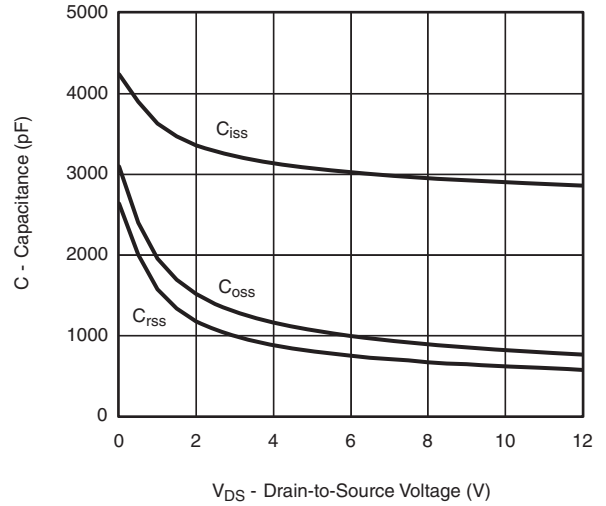
TYPICAL CHARACTERISTICS 25°C unless otherwise noted



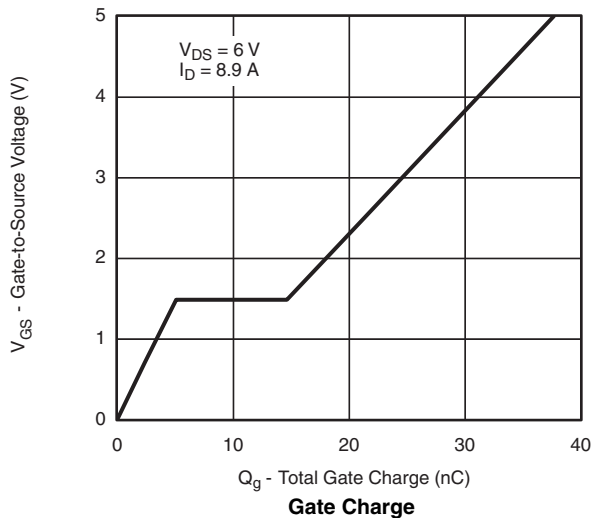
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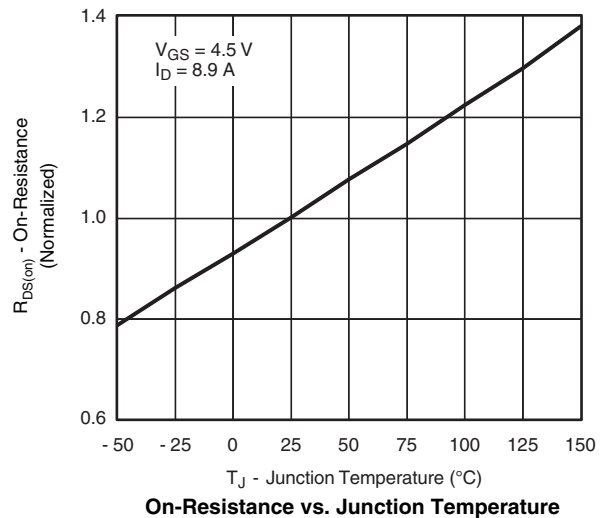
On-Resistance vs. Drain Current



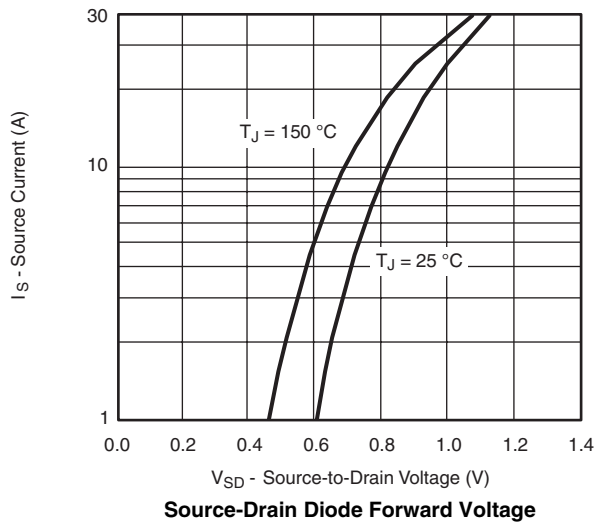
Capacitance



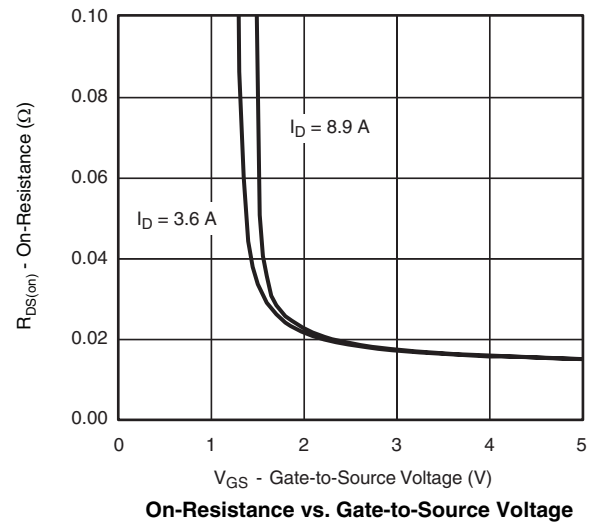
Gate Charge



On-Resistance vs. Junction Temperature

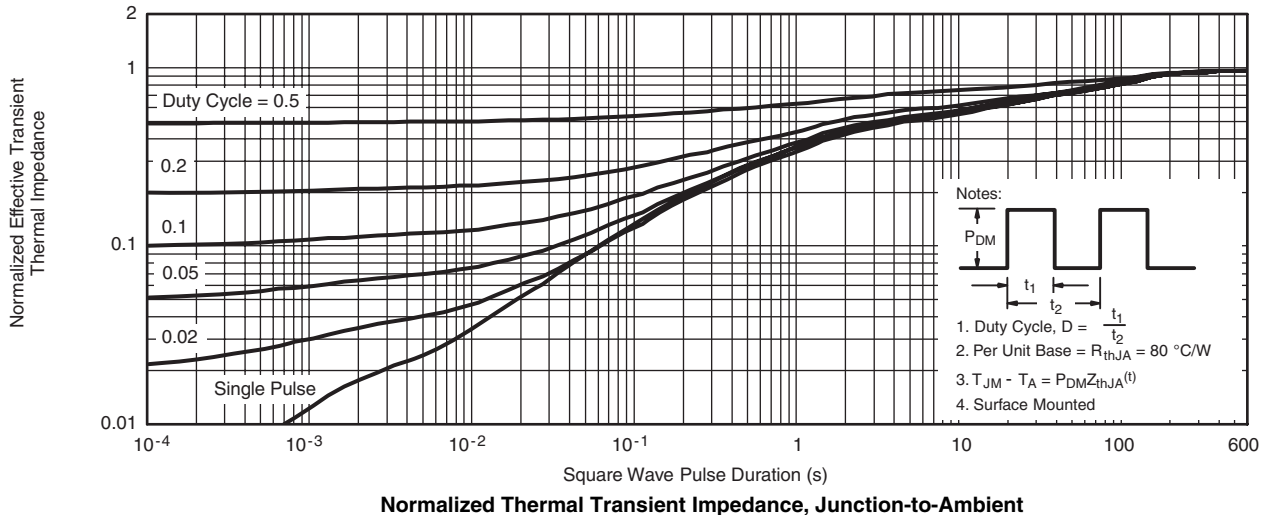
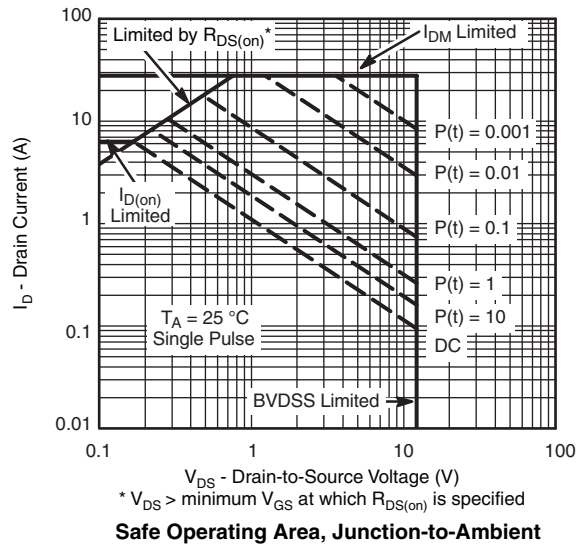
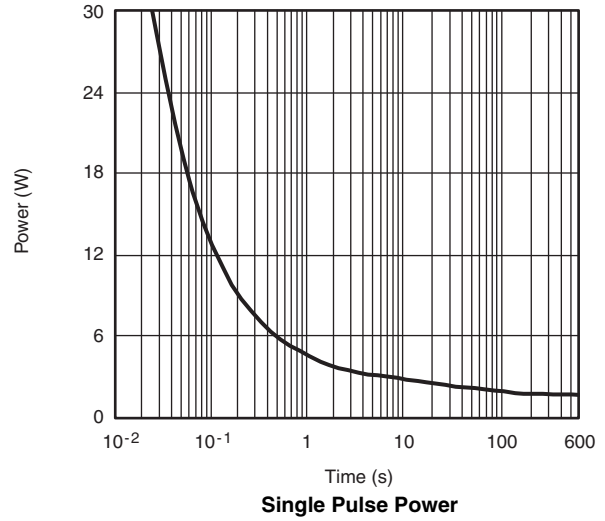
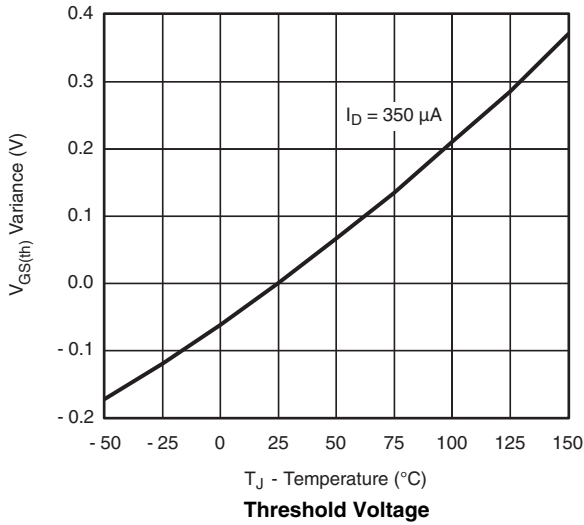


Source-Drain Diode Forward Voltage

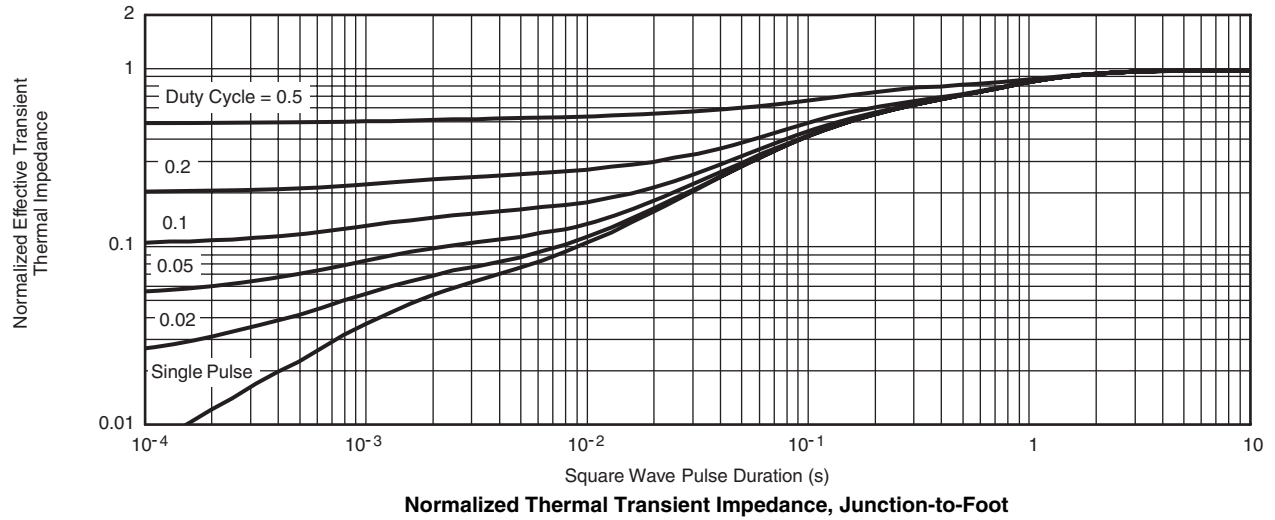


On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C unless otherwise noted



TYPICAL CHARACTERISTICS 25 °C unless otherwise noted



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SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



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